

RB520G-30-AH

Silicon Epitaxial Planar Schottky Barrier Diode

Features

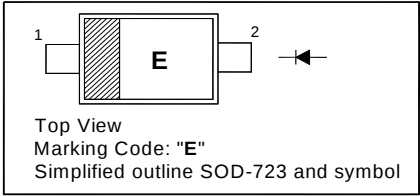
- Ultra Small mold type
- Low I_R
- High reliability
- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant

Applications

- Low current rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

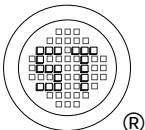


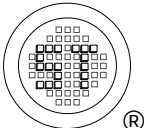
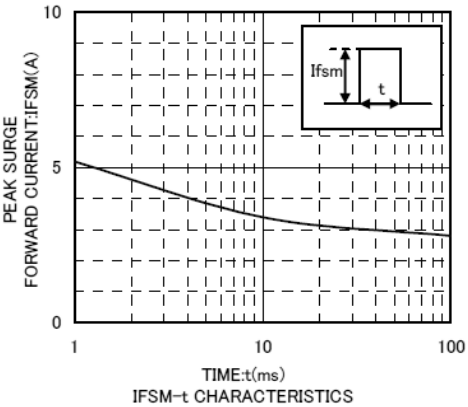
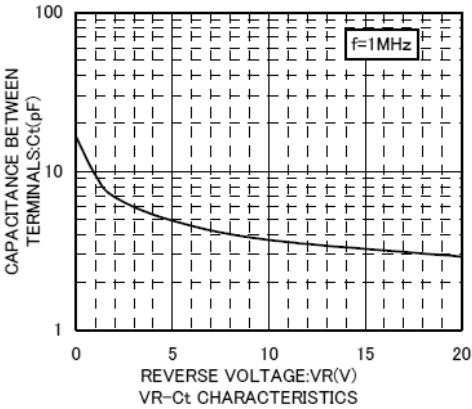
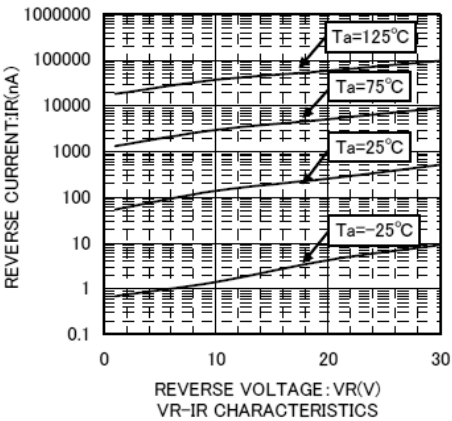
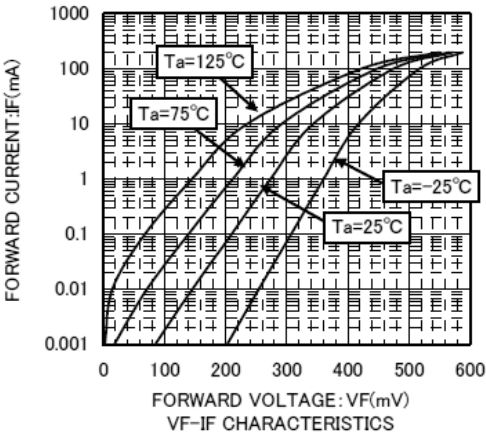
Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average rectified forward current	$I_{F(AV)}$	100	mA
Peak Forward Surge Current (8.3 ms)	I_{FSM}	500	mA
Junction Temperature	T_j	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^{\circ}\text{C}$

Characteristics at $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.45	V
Reverse Current at $V_R = 10\text{ V}$	I_R	0.5	μA





PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-723

Package Outline Dimensions (Units: mm)

